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Sheet 2 of 2

Complete if Known

Application Number	10/799,140
Filing Date	03/12/2004
First Named Inventor	Slater
Group Art Unit	2825 2823
Examiner Name	L. H. Malsawma
Attorney Docket Number	5000.113B

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
ALM	15	SPIES (aka "Spiess"), Aluminum Implantation of p-SiC for ohmic contacts, First European Conference on Silicon Carbide and Related Materials (ECSCRM 96), Oct. 6-9, 1996, pp. 1414-1419, Vol. 6, no. 10, Elsevier, Switzerland	
ALM	16	DEV ALOK et al, Low Contact Resistivity Ohmic Contacts to 6H-Silicon Carbide, Proceedings of the International Electron Devices Meeting, 1993, pp. 691-694, IEEE, New York	
ALM	17	CHEN et al., Contact Resistivity of Re, Pt and Ta Films on n-Type Beta-SiC: Preliminary Results, Materials Science and Engineering, 01/01/1995, pp. 185-189, Vol. B29, no. 1/03, Elsevier Sequoia, Lausanne	
ALM	18	PORTER et al, A critical review of ohmic and rectifying contacts for silicon carbide, Materials Science and Engineering, 11-01-1995, pp. 83-105, Vol. B34, no. 2/03, Elsevier Sequoia, Lausanne	
ALM	19	A. MOKI et al.; Low Resistivity As-Deposited Ohmic Contacts to 3C-SiC; Journal of Electronic Materials; 1995; pp. 315-318; Vol. 24, No. 4	
ALM	20	T. TADAO et al.; Lowering the Annealing Temperature of Ni/SiC for Ohmic Contacts under N(2) Gas, and Application to a UV Sensor; Materials Science Forum; pp. 989-992; Vols. 338-342 (2000)	

Examiner Signature

L. H. Malsawma

Date

Considered

2/2/2005

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